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N THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF:

:

Hironobu KON et al

: GROUP ART UNIT:

SERIAL NO. 09/684,904

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FILED: October 10, 2000

: EXAMINER:

FOR: VOLTAGE-DRIVEN POWER

SEMICONDUCTOR DEVICE

SUPPLEMENTAL PRELIMINARY AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS WASHINGTON, D.C. 20231

SIR:

Prior to examination on the merits, and further to the Preliminary Amendment filed on October 10, 2000, please amend the above-identified application as follows:

IN THE CLAIMS

Please cancel Claims 19-22, without prejudice or disclaimer.

Please add new Claims 23-30, as follows:

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- --23. (New) An injection enhanced gate transistor (IEGT) made of a semiconductor chip, comprising:
 - a collector formed on one side of said semiconductor chip;
- a gate formed on an opposing side which opposes said one side of the semiconductor chip;
 - a main emitter formed on said opposing side of the semiconductor chip; and

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